

1-Mbit (64K x 16) Static RAM

Features

• Temperature Ranges

— Commercial: 0°C to 70°C — Industrial: –40°C to 85°C — Automotive: –40°C to 125°C

High speed

- t_{AA} = 10 ns (Commercial & Industrial)

- $t_{AA} = 15 \text{ ns (Automotive)}$

CMOS for optimum speed/power

· Low active power

— 825 mW (max.)

· Automatic power-down when deselected

Independent control of upper and lower bits

Available in 44-pin TSOP II and 400-mil SOJ

• Also available in Lead (Pb)-Free 44-pin TSOP II

Functional Description^[1]

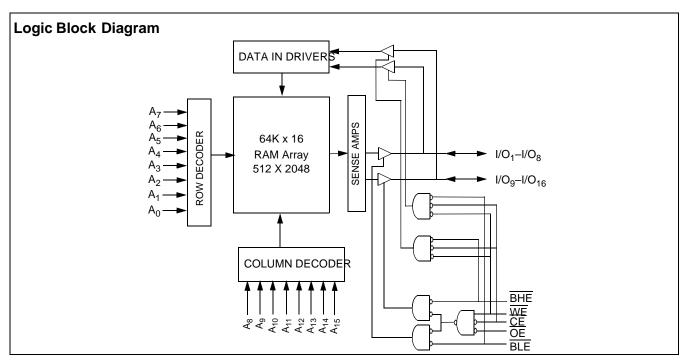
The CY7C1021B/10211B is a high-performance CMOS static RAM organized as 65,536 words by 16 bits. This device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking Chip Enable (CE) and Write Enable (WE) inputs LOW. If Byte Low Enable (BLE) is LOW, then data from I/O pins (I/O₁ through I/O₈), is written into the location specified on the address pins (A0 through A₁₅). If Byte High Enable (BHE) is LOW, then data from I/O pins (I/O₉ through I/O₁₆) is written into the location specified on the address pins (A_0 through A_{15}).

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing the Write Enable (WE) HIGH. If Byte Low Enable (BLE) is LOW, then data from the memory location specified by the address pins will appear on I/O₁ to I/O₈. If Byte High Enable (BHE) is LOW, then data from memory will appear on I/O₉ to I/O₁₆. See the truth table at the back of this data sheet for a complete description of read and write modes.

The input/output pins (I/O₁ through I/O₁₆) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), the BHE and BLE are disabled (BHE, BLE HIGH), or during a write operation (CE LOW, and WE LOW).

The CY7C1021B/10211B is available in standard 44-pin TSOP Type II and 400-mil-wide SOJ packages. Customers should use part number CY7C10211B when ordering parts with 10-ns t_{AA}, and CY7C1021B when ordering 12- and 15-ns



Cypress Semiconductor Corporation Document #: 38-05145 Rev. *B

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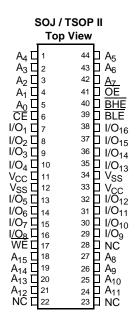
^{1.} For best-practice recommendations, please refer to the Cypress application note "System Design Guidelines" on http://www.cypress.com.



Selection Guide

		7C10211B-10	7C1021B-12	7C1021B-15
Maximum Access Time (ns)		10	12	15
Maximum Operating Current (mA)	Com'l / Ind'l	150	140	130
	Automotive	-	-	150
Maximum CMOS Standby Current (mA)	Com'l / Ind'l	10	10	10
	Automotive	-	-	15
	L Version	0.5	0.5	0.5

Pin Configurations



Pin Definitions

Pin Name	SOJ, TSOP-Pin Number	I/O Type	Description
A ₀ -A ₁₅	1-5,18-21, 24-27, 42-44	Input	Address Inputs used to select one of the address locations.
I/O ₁ –I/O ₁₆	7–10, 13–16, 29–32, 35–38	Input/Output	Bidirectional Data I/O lines . Used as input or output lines depending on operation.
NC	22, 23, 28	No Connect	No Connects. Not connected to the die.
WE	17	Input/Control	Write Enable Input, active LOW . When selected LOW, a Write is conducted. When deselected HIGH, a Read is conducted.
CE	6	Input/Control	Chip Enable Input, active LOW. When LOW, selects the chip. When HIGH, deselects the chip.
BHE, BLE	39, 40	Input/Control	Byte Write Select Inputs, active LOW. $\overline{\rm BLE}$ controls I/O ₈ –I/O ₁ , $\overline{\rm BHE}$ controls I/O ₁₆ –I/O ₉ .
ŌĒ	41	Input/Control	Output Enable, active LOW. Controls the direction of the I/O pins. When LOW, the I/O pins are allowed to behave as outputs. When deasserted HIGH, I/O pins are three-stated, and act as input data pins.
V _{SS}	12, 34	Ground	Ground for the device . Should be connected to ground of the system.
V _{CC}	11, 33	Power Supply	Power Supply inputs to the device.

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Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.) Storage Temperature-65°C to +150°C Ambient Temperature with Power Applied......-55°C to +125°C Supply Voltage on V_{CC} to Relative GND^[2] –0.5V to +7.0V DC Voltage Applied to Outputs in High Z State $^{[2]}$ -0.5V to V_{CC} +0.5V DC Input Voltage^[2].....-0.5V to V_{CC}+0.5V Current into Outputs (LOW)20 mA

Static Discharge Voltage	.>2001V
(per MIL-STD-883, Method 3015)	
Latch-Up Current	>200 mA

Operating Range

Range	Ambient Temperature (T _A) ^[3]	V _{cc}
Commercial	0°C to +70°C	5V ± 10%
Industrial	–40°C to +85°C	5V ± 10%
Automotive	–40°C to +125°C	5V ± 10%

Electrical Characteristics Over the Operating Range

		Test		7C102	11B-10	7C102	21B-12	7C102	1B-15	
Parameter	Description	Condition	ons	Min.	Max.	Min.	Max.	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	$V_{CC} = Min., I_{OH} = -4.0$	mA	2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	V_{CC} = Min., I_{OL} = 8.0 m	ıA		0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage			2.2	6.0	2.2	6.0	2.2	6.0	V
V _{IL}	Input LOW Voltage ^[2]			-0.5	0.8	-0.5	0.8	-0.5	0.8	V
I _{IX}	Input Load	$GND \leq V_I \leq V_CC$	Com'l / Ind'l	-1	+1	-1	+1	-1	+1	μΑ
	Current		Automotive					-4	+4	μΑ
I_{OZ}	Output Leakage $GND \le V_1 \le V_{CC}$,	Com'l / Ind'l	-1	+1	-1	+1	-1	+1	μΑ	
	Current	Output Disabled	Automotive					-4	+4	μΑ
los	Output Short Circuit Current ^[4]	$V_{CC} = Max., V_{OUT} = GI$	ND		-300		-300		-300	mA
Icc	V _{CC} Operating	V _{CC} = Max., I _{OUT} =	Com'l / Ind'l		150		140		130	mA
	Supply Current	0 mA, $f = f_{MAX} = 1/t_{RC}$	Automotive						150	mA
I _{SB1}	Automatic CE	Max. V_{CC} , $\overline{CE} \ge V_{IH}$	Com'l / Ind'l		40		40		40	mA
	Power-Down Current—TTL Inputs	$V_{IN} \ge V_{IH} \text{ or } V_{IN} \le V_{IL}, f$ = f_{MAX}	Automotive						50	mA
I _{SB2}	Automatic CE	Max. V_{CC} , $\overline{CE} \ge V_{CC}$ –	Com'l / Ind'l		10		10		10	mA
	Power-Down Current—CMOS	$0.3V$, $V_{IN} \ge V_{CC} - 0.3V$, or $V_{IN} \le 0.3V$, $f = 0$	Automotive						15	mA
	Inputs		L Version		0.5		0.5		0.5	mA

Thermal Resistance^[5]

Parameter	Description	Test Conditions	44-lead SOJ	44-lead TSOP-II	Unit
- 3/1	(Junction to Ambient)	procedures for measuring thermal impedance,	64.32	76.89	°C/W
00	Thermal Resistance (Junction to Case)	per EIA / JESD51.	31.03	14.28	°C/W

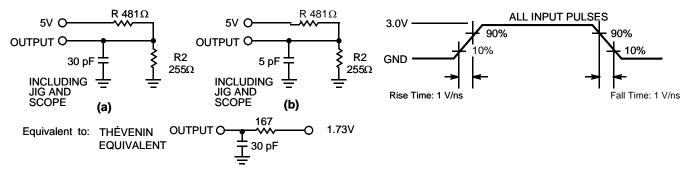
- 2. V_{IL} (min.) = -2.0V and V_{IH} (max) = V_{CC} + 0.5V for pulse durations of less than 20 ns. 3. T_A is the "Instant On" case temperature.
- 4. Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
- 5. Tested initially and after any design or process changes that may affect these parameters.



Capacitance^[5]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	$T_A = 25^{\circ}C$, $f = 1$ MHz,	8	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.0V$	8	pF

AC Test Loads and Waveforms



Switching Characteristics^[6] Over the Operating Range

		7C102	7C10211B-10		7C1021B-12		7C1021B-15	
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Read Cycle		•	•	•	•	•	•	
t _{RC}	Read Cycle Time	10		12		15		ns
t _{AA}	Address to Data Valid		10		12		15	ns
t _{OHA}	Data Hold from Address Change	3		3		3		ns
t _{ACE}	CE LOW to Data Valid		10		12		15	ns
t _{DOE}	OE LOW to Data Valid		5		6		7	ns
t _{LZOE}	OE LOW to Low Z ^[7]	0		0		0		ns
t _{HZOE}	OE HIGH to High Z ^[7, 8]		5		6		7	ns
t _{LZCE}	CE LOW to Low Z ^[7]	3		3		3		ns
t _{HZCE}	CE HIGH to High Z ^[7, 8]		5		6		7	ns
t _{PU}	CE LOW to Power-Up	0		0		0		ns
t _{PD}	CE HIGH to Power-Down		10		12		15	ns
t _{DBE}	Byte Enable to Data Valid		5		6		7	ns
t _{LZBE}	Byte Enable to Low Z	0		0		0		ns
t _{HZBE}	Byte Disable to High Z		5		6		7	ns
Write Cycle ^[9]							•	•
t _{WC}	Write Cycle Time	10		12		15		ns
t _{SCE}	CE LOW to Write End	8		9		10		ns
t _{AW}	Address Set-Up to Write End	7		8		10		ns
t _{HA}	Address Hold from Write End	0		0		0		ns
t _{SA}	Address Set-Up to Write Start	0		0		0		ns
t _{SD}	Data Set-Up to Write End	5		6		8		ns

^{6.} Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified

 ¹⁰L/loH and 30-pF load capacitance.
 At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
 t_{HZOE}, t_{HZBE}, t_{HZCE}, and t_{HZWE} are specified with a load capacitance of 5 <u>p</u>F as in <u>part (b)</u> of AC <u>Test Loads</u>. Transition is <u>measured ±500 mV</u> from steady-state voltage.
 The internal write time of the memory is defined by the overlap of CE LOW, WE LOW and BHE / BLE LOW. CE, WE and BHE / BLE must be LOW to initiate a write, and the transition of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.

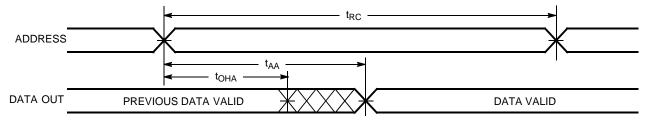


Switching Characteristics^[6] Over the Operating Range (continued)

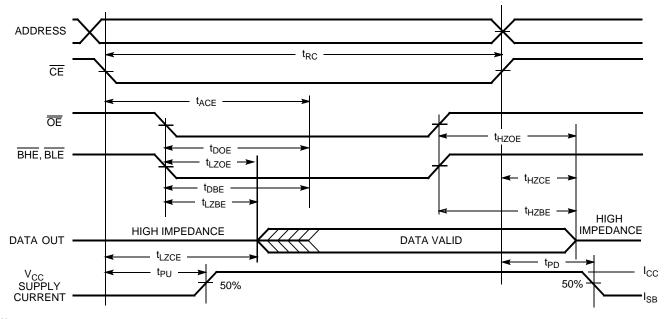
		7C10211B-10		7C1021B-12 7C102		21B-15		
Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t _{HD}	Data Hold from Write End	0		0		0		ns
t _{LZWE}	WE HIGH to Low Z ^[7]	3		3		3		ns
t _{HZWE}	WE LOW to High Z ^[7, 8]		5		6		7	ns
t _{BW}	Byte Enable to End of Write	7		8		9		ns

Switching Waveforms

Read Cycle No. 1^[10, 11]



Read Cycle No. 2 (OE Controlled)[11, 12]



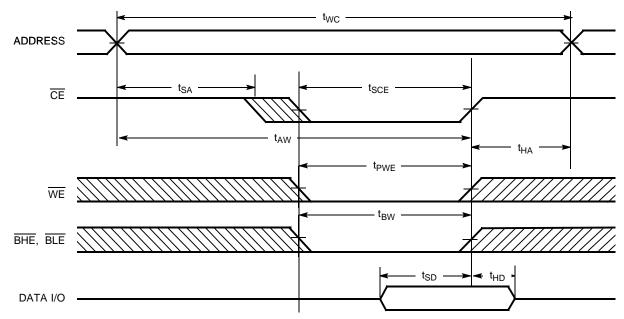
10. <u>Devi</u>ce is continuously selected. <u>OE</u>, <u>CE</u>, <u>BHE</u> and/or <u>BHE</u> = V_{IL}.

11. <u>WE</u> is HIGH for read cycle.

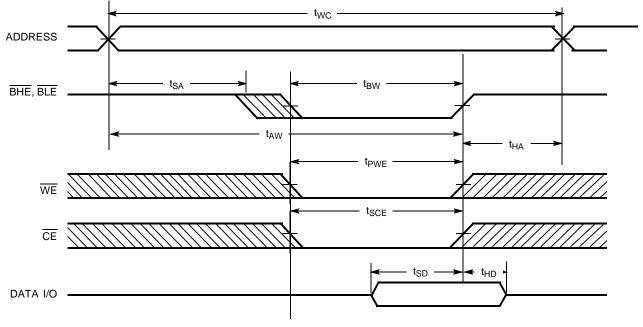


Switching Waveforms (continued)

Write Cycle No. 1 (CE Controlled)[13, 14]



Write Cycle No. 2 (BLE or BHE Controlled)



Notes:

- 12. Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.

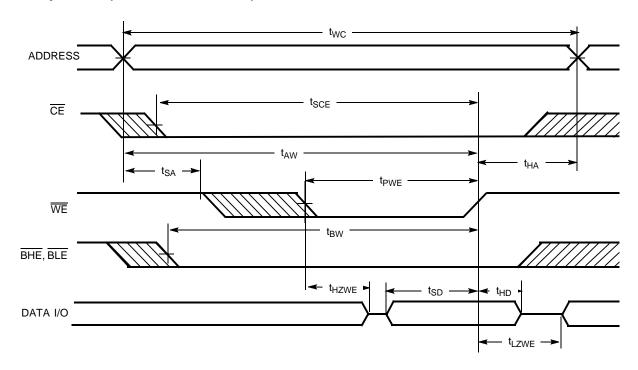
 13. Data I/O is high impedance if $\overline{\text{OE}}$ or $\overline{\text{BHE}}$ and/or $\overline{\text{BLE}} = V_{\text{IH}}$.

 14. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ going HIGH, the output remains in a high-impedance state.



Switching Waveforms (continued)

Write Cycle No. 3 (WE Controlled, OE LOW)



Truth Table

CE	OE	WE	BLE	BHE	I/O ₁ –I/O ₈	I/O ₉ -I/O ₁₆	Mode	Power
Н	Х	Χ	Χ	X	High Z	High Z	Power-Down	Standby (I _{SB})
L	L	Н	L	L	Data Out	Data Out	Read - All bits	Active (I _{CC})
			L	Н	Data Out	High Z	Read - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data Out	Read - Upper bits only	Active (I _{CC})
L	Х	L	L	L	Data In	Data In	Write - All bits	Active (I _{CC})
			L	Н	Data In	High Z	Write - Lower bits only	Active (I _{CC})
			Н	L	High Z	Data In	Write - Upper bits only	Active (I _{CC})
L	Н	Н	Χ	X	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})
L	Χ	Χ	Н	Н	High Z	High Z	Selected, Outputs Disabled	Active (I _{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
10	CY7C10211B-10VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C10211B-10ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C10211BL-10ZC	Z44	44-Lead TSOP Type II	Commercial
12	CY7C1021B-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1021B-12VXC	V34	44-Lead (400-Mil) Molded SOJ (Pb-Free)	Commercial
	CY7C1021B-12VI	V34	44-Lead (400-Mil) Molded SOJ	Industrial
	CY7C1021B-12VXI	V34	44-Lead (400-Mil) Molded SOJ (Pb-Free)	Industrial
	CY7C1021BL-12VC	V34	44-Lead (400-Mil) Molded SOJ	Commercial
	CY7C1021B-12ZC	Z44	44-Lead TSOP Type II	Commercial
	CY7C1021B-12ZXC	Z44	44-Lead TSOP Type II (Pb-Free)	Commercial

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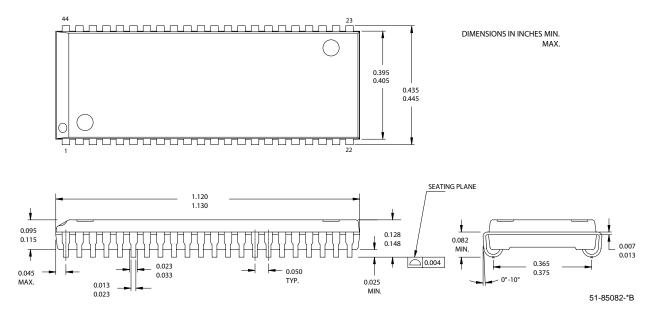


Ordering Information (continued)

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
12	CY7C1021B-12ZI	Z44	44-Lead TSOP Type II	Industrial
	CY7C1021BL-12ZC	Z44	44-Lead TSOP Type II	Commercial
15	CY7C1021B-15VC	V34	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021B-15VXC	V34	44-pin (400-Mil) Molded SOJ (Pb-Free)	Commercial
	CY7C1021B-15VI	V34	44-pin (400-Mil) Molded SOJ	Industrial
	CY7C1021B-15VXI	V34	44-pin (400-Mil) Molded SOJ (Pb-Free)	Industrial
	CY7C1021BL-15VC	V34	44-pin (400-Mil) Molded SOJ	Commercial
	CY7C1021BL-15VXC	V34	44-pin (400-Mil) Molded SOJ (Pb-Free)	Commercial
	CY7C1021B-15VE	V34	44-pin (400-Mil) Molded SOJ	Automotive
	CY7C1021B-15VXE	V34	44-pin (400-Mil) Molded SOJ (Pb-Free)	Automotive
	CY7C1021B-15ZC	Z44	44-pin TSOP Type II	Commercial
	CY7C1021B-15ZXC	Z44	44-pin TSOP Type II (Pb-Free)	Commercial
	CY7C1021B-15ZI	Z44	44-pin TSOP Type II	Industrial
	CY7C1021B-15ZXI	Z44	44-pin TSOP Type II (Pb-Free)	Industrial
	CY7C1021BL-15ZC	Z44	44-pin TSOP Type II	Commercial
	CY7C1021BL-15ZXC	Z44	44-pin TSOP Type II (Pb-Free)	Commercial
	CY7C1021B-15ZE	Z44	44-pin TSOP Type II	Automotive
	CY7C1021B-15ZSXE	Z44	44-pin TSOP Type II (Pb-Free)	Automotive

Package Diagrams

44-Lead (400-Mil) Molded SOJ V34





Package Diagrams (continued)

DIMENSION IN MM (INCH) MAX NIN. 44-Pin TSOP II Z44 ²² Aarrraarraarraarra 8888888888888888888888 EJECTOR PIN TOP VIEW BOTTOM VIEW 10.262 (0.404) 0.800 BSC BASE PLANE **△**0.10 (.004) 0.597 (0.0235) SEATING PLANE 51-85087-*A

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Document History Page

Document Title: CY7C1021B/CY7C10211B (64K x 16) Static RAM Document Number: 38-05145				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	109889	09/22/01	SZV	Change from Spec number: 38-00951 to 38-05145
*A	238454	See ECN	RKF	Added Automotive Specs to Data Sheet Added Pb-Free device offering in the Ordering Information
*B	361795	See ECN	SYT	Added Pb-Free offerings in the Ordering Information

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